2N5460-2N5465
P-Channel JFET

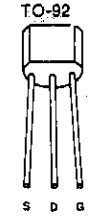
1

ABSOLUTE MAXIMUM RATINGS
(T_A = 25°C unless otherwise noted)

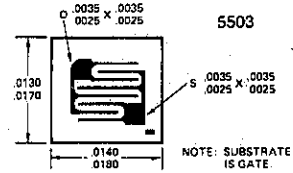
Drain-Gate or Source-Gate Voltage
- 2N5460 - 2N5462 ..... 40V
- 2N5463 - 2N5465 ..... 60V

Gate Current ..... 10 mA
Storage Temperature Range ..... -65°C to +200°C
Operating Temperature Range ..... -55°C to +150°C
Lead Temperature (Soldering, 10 sec.) ..... +300°C
Power Dissipation ..... 310 mW
- Derate above 25°C ..... 2.8 mW/°C

PIN CONFIGURATION
TO-92



CHIP TOPOGRAPHY



ORDERING INFORMATION*

TO-92	WAFER	DICE
2N5460	2N5460/W	2N5460/D
2N5461	2N5461/W	2N5461/D
2N5462	2N5462/W	2N5462/D
2N5463	2N5463/W	2N5463/D
2N5464	2N5464/W	2N5464/D
2N5465	2N5465/W	2N5465/D

*When ordering wafer/dice refer to Appendix B-23.

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

	PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITIONS	
BV_{GSS}	Gate-Source Breakdown Voltage	2N5460, 2N5461, 2N5462	40			V	I_G = 10 μAdc, V_{DS} = 0	
		2N5463, 2N5464, 2N5465	60					
$V_{GS(off)}$	Gate-Source Cutoff Voltage	2N5460, 2N5463	0.75		6.0	V	V_{DS} = 15 Vdc, I_D = 1.0 μAdc	
		2N5461, 2N5464	1.0		7.5			
		2N5462, 2N5465	1.8		9.0			
I_{GSSR}	Gate Reverse Current	2N5460, 2N5461, 2N5462			5.0	nA	V_{DS} = 0	V_{GS} = 20V
		2N5463, 2N5464, 2N5465			5.0			V_{GS} = 30V
	T_A = 100°C	2N5460, 2N5461, 2N5462			1.0	μA		V_{GS} = 20V
		2N5463, 2N5464, 2N5465			1.0			V_{GS} = 30V
I_{DSS}	Zero-Gate Voltage Drain Current	2N5460, 2N5463	-1.0		-5.0	mA	V_{DS} = -15V	V_{GS} = 0
		2N5461, 2N5464	-2.0		-9.0			
		2N5462, 2N5465	-4.0		-16			
V_{GS}	Gate-Source Voltage	2N5460, 2N5463	0.5		4.0	V		I_D = 0.1 mA
		2N5461, 2N5464	0.8		4.5			I_D = -0.2 mA
		2N5462, 2N5465	1.5		6.0			I_D = -0.4 mA
g_{fs}	Forward Transadmittance	2N5460, 2N5463	1000		4000	μmho	V_{DS} = -15V, V_{GS} = 0V	f = 1.0 kHz
		2N5461, 2N5464	1500		5000			
		2N5462, 2N5465	2000		6000			
g_{os}	Output Admittance				75	μmho		
C_{iss}	Input Capacitance			5.0	7	pF		
C_{rss}	Reverse Transfer Capacitance			1.0	2.0	pF		
NF	Common-Source Noise Figure			1.0	2.5	dB		f = 100 Hz, BW = 1.0 Hz, R_G = 1.0 MΩ
$\bar{e}_n$	Equivalent Short-Circuit Input Noise Voltage			.60	115	$nV/\sqrt{Hz}$		